04-22-04

Express Mail No. EV 346 810 864 US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Bruno GHYSELEN et al.

Confirmation No. 7267

Application No: 10/686,082

Group Art Unit: 2812

Filing Date: October 14, 2003

Examiner:

Atty. Docket No.: 4717-11400

For: PREVENTIVE TREATMENT METHOD FOR A MULTILAYER SEMICONDUCTOR STRUCTURE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, applicants submit herewith nine (9) references for the Examiner's review and consideration. These references were cited in the Preliminary Search Report and a copy is enclosed.

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee is believed to be due for the filing of this statement as it is being submitted prior to an initial office action for this application. Should any fees be required, however, please charge such fees to Winston & Strawn **LLP** Deposit Account No. 50-1814.

Respectfully submitted,

Date: 4/21/04

Allan A. Fanucci (Reg. No. 30,256)

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CUSTOMER NO. 28765
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Enclosures

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LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION SERIAL NO.:
4717-11400	10/686, 082
APPLICANT: Bruno GHYSELEN et al.	
FILING DATE: October 14, 2003	**GROUP:** 2812

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	4,771,016	9/1988	Bajor et al.	437	180	
	AB	5,517,047	5/1996	Linn et al.	257	347	
	AC	6,313,012 B1	11/2001	Horiuchi et al.	438	459	
	AD	6,410,938 B1	6/2002	Xiang	257	49	
	AE	2002/0070454 A1	6/2002	Yasukawa	257	760	
	AF	2004/0023468 A1	2/2004	Ghyselen et al.	438	455	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AG	FR 2 835 096 w/ English Abstract	7/2003	France			X	
	AH	WO 03063214 A2 (English Abstract of FR2835095)	7/2003	PCT			X	
	AI							

OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	AJ	N. Tate et al., "Defect Reduction of Bonded SOI Wafers by Post Anneal Process in H_2 Ambient," Proceedings 1998 IEEE International SOI Conference, pp. 141-142 (1998)
	AK	
	AL	
	AM	

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with **MPEP 609**; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.